# imall

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### SINGLE BUFFER GATE WITH 3-STATE OUTPUT

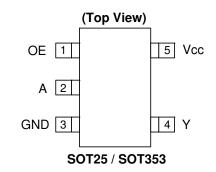
#### Description

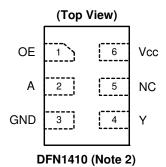
The 74LVCE1G126 is a single non-inverting buffer/bus driver with a 3-state output. The output enters a high impedance state when a LOW-level is applied to the output enable (OE) pin. The device is designed for operation with a power supply range of 1.4V to 5.5V. The inputs are tolerant to 5.5V allowing this device to be used in a mixed voltage environment. The device is fully specified for partial power down applications using  $I_{OFF}$ . The  $I_{OFF}$  circuitry disables the output preventing damaging current backflow when the device is powered down.

#### Features

- Extended Supply Voltage Range from 1.4 to 5.5V
- · Switching speed characterized for operation at 1.5V
- Offers 30% speed improvement over LVC at 1.8V.
- ± 24mA Output Drive at 3.3V
- CMOS low power consumption
- IOFF Supports Partial-Power-Down Mode Operation
- Inputs accept up to 5.5V
- ESD Protection Tested per JESD 22
  Exceeds 200-V Machine Model (A115-A)
  Exceeds 2000-V Human Body Model (A114-A)
- Latch-Up Exceeds 100mA per JESD 78, Class II
- Range of Package Options
- · Direct Interface with TTL Levels
- SOT25, SOT353 and DFN1410: Assembled with "Green" Molding Compound (no Br, Sb)
- Lead Free Finish/ RoHS Compliant (Note 1)

#### **Pin Assignments**





#### Applications

- Voltage Level Shifting
- Bus Driver / Repeater
- Power Down Signal Isolation
- General Purpose Logic
  - Wide array of products such as.
  - PCs, networking, notebooks, netbooks, PDAs
  - o Computer peripherals, hard drives, CD/DVD ROM
  - o TV, DVD, DVR, set top box
  - o Cell Phones, Personal Navigation / GPS
  - o MP3 players ,Cameras, Video Recorders
- Notes: 1. EU Directive 2002/95/EC (RoHS). All applicable RoHS exemptions applied. Please visit our website at http://www.diodes.com/products/lead\_free.html.
  - 2. Pin 2 and pin 5 of the DFN1410 package are internally connected.

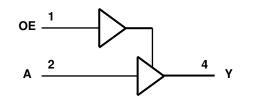


## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Pin Descriptions**

Pin Name	Description
OE	Output Enable (active high)
А	Data Input
GND	Ground
Y	Data Output
Vcc	Supply Voltage

### Logic Diagram



### **Function Table**

Inp	Output				
OE					
Н	Н	Н			
Н	L	L			
L	Х	Z			



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Absolute Maximum Ratings (Note 3)

Symbol	Description	Rating	Unit
ESD HBM	Human Body Model ESD Protection	2	KV
ESD MM	Machine Model ESD Protection	200	V
V <sub>CC</sub>	Supply Voltage Range	-0.5 to 6.5	V
Vi	Input Voltage Range	-0.5 to 6.5	V
Vo	Voltage applied to output in high impedance or IOFF state	-0.5 to 6.5	V
Vo	Voltage applied to output in high or low state	-0.3 to V <sub>CC</sub> +0.5	V
I <sub>IK</sub>	Input Clamp Current V <sub>I</sub> <0	-50	mA
Ι <sub>ΟΚ</sub>	Output Clamp Current	-50	mA
Ι <sub>Ο</sub>	Continuous output current	±50	mA
	Continuous current through Vdd or GND	±100	mA
TJ	Operating Junction Temperature	-40 to 150	°C
T <sub>STG</sub>	Storage Temperature	-65 to 150	°C

Note: 3. Stresses beyond the absolute maximum may result in immediate failure or reduced reliability. These are stress values and device operation should be within recommend values.

74LVCE1G126 Document number: DS32217 Rev. 3 - 2



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## **Recommended Operating Conditions (Note 4)**

Symbol		Parameter	Min	Max	Unit
N/		Operating	1.4	5.5	V
$V_{CC}$	Operating Voltage	Data retention only	1.2		V
		V <sub>CC</sub> = 1.4 V to 1.95 V	0.65 X V <sub>CC</sub>		
V 11		$V_{\rm CC}$ = 2.3 V to 2.7 V	1.7		V
V <sub>IH</sub>	High Level Input Voltage	V <sub>CC</sub> = 3 V to 3.6 V	2		V
		$V_{\rm CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$	0.7 X V <sub>CC</sub>		
		V <sub>CC</sub> = 1.4 V to 1.95 V		$0.35 \text{ X V}_{CC}$	
V		$V_{\rm CC} = 2.3 \text{ V}$ to 2.7 V		0.7	V
$V_{IL}$	Low Level Input Voltage	V <sub>CC</sub> = 3 V to 3.6 V		0.8	V
		$V_{\rm CC} = 4.5 \text{ V} \text{ to } 5.5 \text{ V}$		0.3 X V <sub>CC</sub>	
VI	Input Voltage		0	5.5	V
Vo	Output Voltage		0	V <sub>CC</sub>	V
		Vcc=1.4 V		-3	·
	High Level Output	V <sub>CC</sub> = 1.65 V		-4	
		$V_{\rm CC} = 2.3  \rm V$		-8	
I <sub>OH</sub>	Current			-16	mA
		$V_{CC} = 3 V$		-24	
		$V_{\rm CC} = 4.5  \rm V$		-32	
		Vcc=1.4 V		3	
		V <sub>CC</sub> = 1.65 V		4	
	Low Level Output	$V_{\rm CC} = 2.3  \rm V$		8	mA
I <sub>OL</sub>	Current			16	
		$V_{CC} = 3 V$		24	
		$V_{\rm CC} = 4.5  \rm V$		32	
		$V_{\rm CC} = 1.4$ to 3V		20	
Δt/ΔV	Input transition rise or fall	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$		10	ns/V
rate	rate	$V_{CC} = 5 V \pm 0.5 V$		5	
T <sub>A</sub>	Operating free-air temperature		-40	85	°C

Note: 4. Unused inputs should be held at Vcc or Ground.



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Electrical Characteristics (All typical values are at Vcc = 3.3V, T<sub>A</sub> = 25°C)

Symbol	Parameter	<b>Test Conditions</b>	Vcc	Min	Тур.	Max	Unit	
		I <sub>OH</sub> = -100μA	1.4 V to 5.5V	$V_{CC} - 0.1$				
		I <sub>OH</sub> = -3mA	1.4 V	1.05				
		$I_{OH} = -4mA$	1.65 V	1.2				
V <sub>OH</sub>	High Level Output Voltage	I <sub>OH</sub> = -8mA	2.3V	1.9			V	
	Vollage	$I_{OH} = -16mA$	3 V	2.4				
		$I_{OH} = -24mA$	5 V	2.3				
		$I_{OH} = -32mA$	4.5 V	3.8				
		$I_{OL} = 100 \mu A$	1.4 V to 5.5V			0.1		
		$I_{OL} = 3mA$	1.4V			.4		
		$I_{OL} = 4mA$	1.65 V			0.45		
V <sub>OL</sub>	Low Level Output Voltage	$I_{OL} = 8mA$	2.3V			0.3	V	
Vonag	Vollage	$I_{OL} = 16mA$	3 V			0.4	-	
		$I_{OL} = 24mA$	5 V			0.55		
		$I_{OL} = 32mA$	4.5			0.55		
l <sub>i</sub>	Input Current	$V_1 = 5.5 \text{ V or GND}$	0 to 5.5 V			± 5	μA	
I <sub>OFF</sub>	Power Down Leakage Current	$V_1 \text{ or } V_0 = 5.5 V$	0			± 10	μA	
I <sub>oz</sub>	Z State Leakage Current	$V_0 = 0$ to 5.5V	3.6V			10	μA	
I <sub>CC</sub>	Supply Current	$V_1 = 5.5V$ of GND $I_0=0$	1.4 V to 5.5V			10	μA	
$\Delta I_{CC}$	Additional Supply Current	One input at $V_{CC}$ – 0.6 V Other inputs at $V_{CC}$ or GND	3 V to 5.5V			500	μA	
Ci	Input Capacitance	$V_i = V_{CC} - or GND$	3.3		3.5		pF	
		SOT25	(Note 5)		204			
$\theta_{JA}$	Thermal Resistance Junction-to-Ambient	SOT353	(Note 5)		371		°C/W	
		DFN1410	(Note 5)		430			
		SOT25	(Note 5)		52			
$\theta_{\rm JC}$	Thermal Resistance Junction-to-Case	SOT353	(Note 5)		143		°C/W	
	Junction-to-Gase	DFN1410	(Note 5)		190			

Over recommended free-air temperature range (unless otherwise noted)

Note: 5. Test condition for SOT25, SOT353 and DFN1410: Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### **Switching Characteristics**

Daramotor	From	-	-	-	-	-	-	то	Vcc = 1.5 V ± 0.1V		Vcc = 1.8 V ± 0.15V		Vcc = 2.5 V ± 0.2V		Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V		Unit
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Мах	Min	Мах							
t <sub>pd</sub>	А	Y	1.7	6.9	1.1	4.8	0.4	3.6	0.4	3	0.4	3	ns						

Over recommended free-air temperature range, CL = 15pF (see Figure 1)

#### Over recommended free-air temperature range, CL = 30 or 50pF as noted (see Figure 2)

Parameter From		то	± 0.1V			Vcc = 1.8 V Vc ± 0.15V		Vcc = 2.5 V ± 0.2V		Vcc = 3.3 V ± 0.3V		Vcc = 5 V ± 0.5V	
	(Input)	(OUTPUT)	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
t <sub>pd</sub>	А	Y	2.6	8	1.8	5.6	0.8	4.4	0.8	3.6	0.9	3.6	ns
t <sub>en</sub>	OE	Y	2.8	9.4	1.9	6.5	1	5.2	0.9	4.3	0.9	4.3	
t <sub>dis</sub>	OE	Y	1.6	9.8	1.1	6.8	0.8	4.4	0.8	4.5	0.9	3.7	

### **Operating Characteristics**

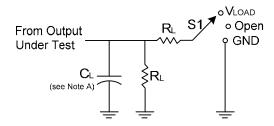
 $T_A = 25 \ ^{o}C$ 

	Parame	ter	Test Conditions	Vcc = 1.5 V TYP	Vcc = 1.8 V TYP	Vcc = 2.5 V TYP	Vcc = 3.3 V TYP	Vcc = 5 V TYP	Unit
	Power	Outputs enabled	f 10 MU	19	19	19	19	19	<b>م</b> ۲
C <sub>pd</sub>	dissipation capacitance	Outputs disabled	f = 10 MHz	2	2	2	3	4	pF



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### **Parameter Measurement Information**



TEST	S1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	Vload
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

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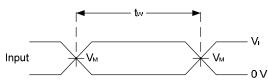
**Voltage Waveform Enable and Disable Times** 

Low and High Level Enabling

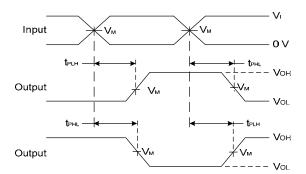
t<sub>PZL</sub>

t<sub>PZH</sub>

Vcc	In	puts	No.	0.	Р.
VCC	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	CL	RL
1.5V±0.1V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ
1.8V±0.15V	V <sub>CC</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ
2.5V±0.2V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	15pF	1MΩ
3.3V±0.3V	3V	≤2.5ns	1.5V	15pF	1MΩ
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	15pF	1MΩ



#### **Voltage Waveform Pulse Duration**



#### Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

- Notes: A. Includes test lead and test apparatus capacitance.
  - B. All pulses are supplied at pulse repetition rate ≤ 10 MHz.
  - C. Inputs are measured separately one transition per measurement.
  - D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis.}$
  - E.  $t_{PZL}$  and  $t_{PZH}$  are the same as  $t_{EN}$ .
  - F.  $t_{PLH}$  and  $t_{PHL}$  are the same as  $t_{PD.}$



Output

Control

Output

Output

Waveform 1 S1 at VLOAD

(see Note B)

Waveform 2

S1 at GND

(see Note B)

#### Figure 1. Load Circuit and Voltage Waveforms

Vi

0 V

VLOAD/2

Vol

Vон

6 OV

Vм

→

🔶 telz

Vol + Va

Vон V<sub>Δ</sub>

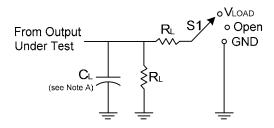
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4



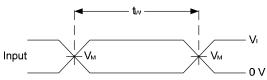
### SINGLE BUFFER GATE WITH 3-STATE OUTPUT

#### Parameter Measurement Information (Continued)

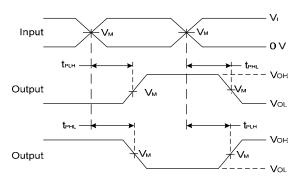


TEST	S1
	-
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	Vload
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

Vcc	Ing	outs	V <sub>M</sub>	CL	RL
	Vı	t <sub>r</sub> /t <sub>f</sub>	• 141	υĽ	
1.5V±0.1V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1KΩ
1.8V±0.15V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	1KΩ
2.5V±0.2V	V <sub>cc</sub>	≤2ns	V <sub>CC</sub> /2	30pF	500Ω
3.3V±0.3V	3V	≤2.5ns	1.5V	50pF	500Ω
5V±0.5V	V <sub>CC</sub>	≤2.5ns	V <sub>CC</sub> /2	50pF	500Ω



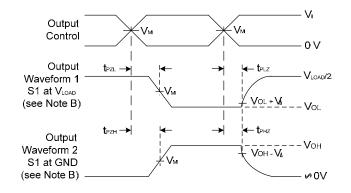
#### **Voltage Waveform Pulse Duration**



#### Voltage Waveform Propagation Delay Times Inverting and Non Inverting Outputs

- Notes: A. Includes test lead and test apparatus capacitance.
  - B. All pulses are supplied at pulse repetition rate  $\leq$  10 MHz.
  - C. Inputs are measured separately one transition per measurement.
  - D.  $t_{PLZ}$  and  $t_{PHZ}$  are the same as  $t_{dis.}$
  - E.  $t_{\text{PZL}}$  and  $t_{\text{PZH}}$  are the same as  $t_{\text{EN0}}$
  - F.  $t_{\text{PLH}}$  and  $t_{\text{PHL}}$  are the same as  $t_{\text{PD.}}$

#### Figure 2. Load Circuit and Voltage Waveforms



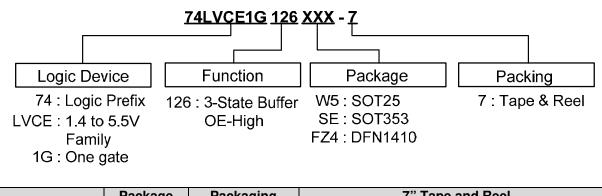
#### Voltage Waveform Enable and Disable Times Low and High Level Enabling

NEW PRODUCT



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

#### **Ordering Information**



	Device	Package Packaging		7" Tape and Reel	
	Device	Code	(Note 5)	Quantity	Part Number Suffix
<b>Pb</b> ,	74LVCE1G126W5-7	W6	SOT25	3000/Tape & Reel	-7
<b>Pb</b> ,	74LVCE1G126SE-7	SE	SOT353	3000/Tape & Reel	-7
<b>Pb</b> ,	74LVCE1G126FZ4-7	FZ4	DFN1410	5000/Tape & Reel	-7

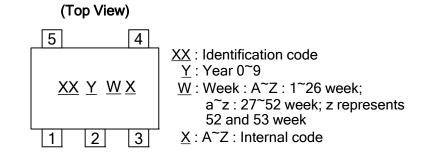
Note: 6. Pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

#### **Marking Information**

#### (1) SOT25 and SOT353



Part Number	Package	Identification Code
74LVCE1G126W5	SOT25	PZ
74LVCE1G126SE	SOT353	PZ

#### (2) DFN1410

#### (Top View)



- $\underline{XX}$  : Identification Code  $\underline{Y}$  : Year : 0~9
  - $\underline{W}$ : Week : A~Z : 1~26 week; a~z : 27~52 week; z represents 52 and 53 week
  - $\underline{X}$ : A~Z : Internal code

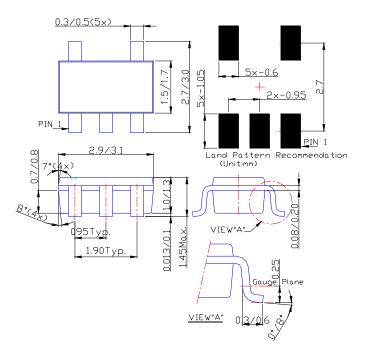
Part Number	Package	Identification Code
74LVCE1G126FZ4	DFN1410	PZ



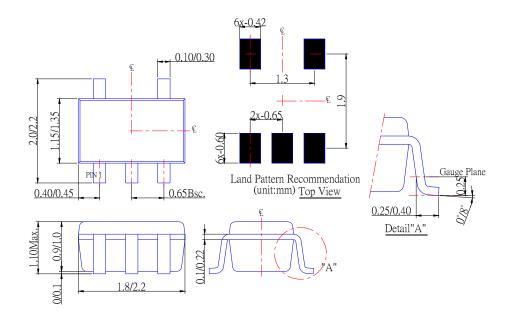
## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Package Outline Dimensions (All Dimensions in mm)

#### (1) Package Type: SOT25



#### (2) Package Type: SOT353



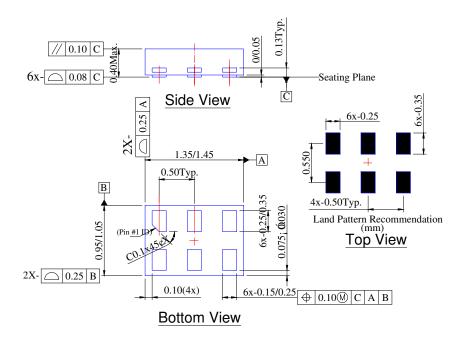
74LVCE1G126 Document number: DS32217 Rev. 3 - 2



## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

## Package Outline Dimensions (All Dimensions in mm)

#### (3) Package Type: DFN1410

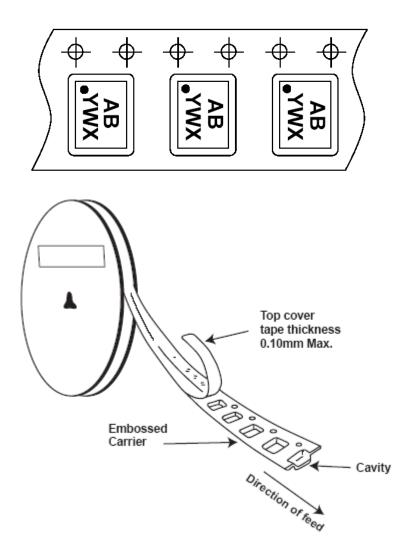


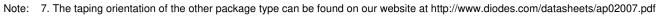


## SINGLE BUFFER GATE WITH 3-STATE OUTPUT

### Taping Orientation (Note 7)

#### For DFN1410







### SINGLE BUFFER GATE WITH 3-STATE OUTPUT

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